## RT1N140X SERIES

**(Transistor)** 

UNIT: mm

Transistor With Resistor For Switching Application Silicon NPN Epitaxial Type

## **DESCRIPTION**

RT1N140X is a one chip transistor with built-in bias resistor, PNP type is RT1P140X.

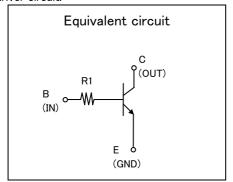
## **FEATURE**

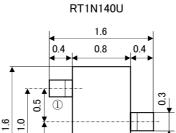
•Built-in bias resistor (R1=10k $\Omega$ )

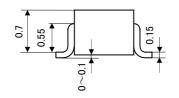
## **APPLICATION**

Inverted circuit, switching circuit, interface

driver circuit.







JEITA: -JEDEC: -

**Terminal Connector** 

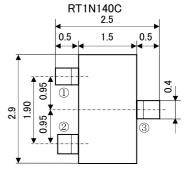
1:Base

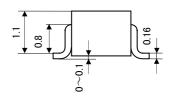
2: Emitter

3: Collector

RT1N140C 2.5

OUTLINE DRAWING





JEITA: SC-59

JEDEC: Similar to TO-236

**Terminal Connector** 

1:Base

2: Emitter

3: Collector

RT1N140M

2.1

1.25

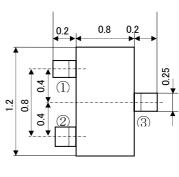
0.425

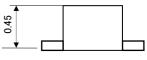
0.425

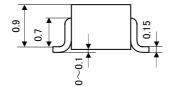
0.65

2.0









JEITA: SC-70 JEDEC: -

**Terminal Connector** 

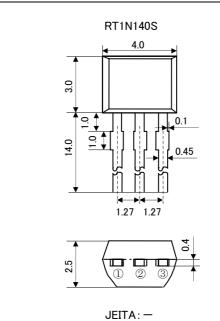
JEITA: -JEDEC: -

**Terminal Connector** 

1:Base

2: Emitter

3: Collector



JEDEC: -

(1): Emitter

3:Base

2: Collector

# RT1N140X SERIES

**(Transistor)** 

Transistor With Resistor
For Switching Application
Silicon NPN Epitaxial Type

## MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING					UNIT
		RT1N140T	RT1N140U	RT1N140M	RT1N140C	RT1N140S	UNIT
V <sub>CBO</sub>	Collector to Base voltage	50					٧
$V_{EBO}$	Emitter to Base voltage	6					V
$V_{CEO}$	Collector to Emitter voltage	50				V	
Ic	Collector current	100					mA
I <sub>CM</sub>	Peak Collector current	200					mA
P <sub>c</sub>	Collector dissipation(Ta=25°C)	125 (※ )	150	200		450	mW
Tj	Junction temperature	+125	+125 +150			°C	
Tstg	Storage temperature	<b>-55∼+125 -55∼+150</b>			°C		

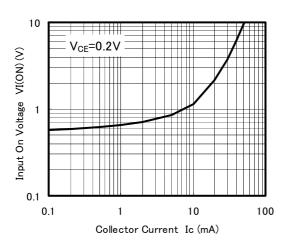
( $\mbox{\em $\times$}$  ) package mounted on 9mm  $\mbox{\em $\times$}$  19mm  $\mbox{\em $\times$}$  1mm glass-epoxy substrate.

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

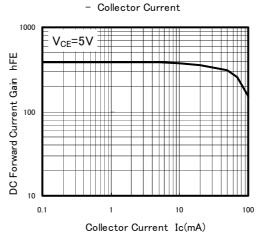
SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	C to E break down voltage	I <sub>C</sub> =100 μ A, R <sub>BE</sub> =∞	50			٧
I <sub>CBO</sub>	Collector cut off current	$V_{CB}$ =50V, $I_{E}$ =0			0.1	μΑ
h <sub>FE</sub>	DC forward current gain	$V_{CE}$ =5V, I $_{C}$ =1mA	100			_
$V_{CE(sat)}$	C to E saturation voltage	$I_{C}$ =10mA, $I_{B}$ =0.5mA		0.1	0.3	٧
R <sub>1</sub>	Input resistance		7	10	13	kΩ
f⊤	Gain band width product	$V_{CE}=6V$ , $I_{E}=-10mA$		200		MHz

## TYPICAL CHARACTERISTICS

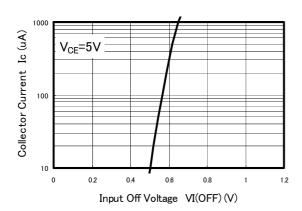




DC Forward Current Gain



Collector Current - Input Off Voltage





Marketing division, Marketing planning department 6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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